



BLW75

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLW75** is Designed for 25V Large-Signal Amplifier Applications, TV Transposers, and Transmitters Operating in Band III.

MAXIMUM RATINGS

I_C	4.0 A
V_{CE}	32 V
V_{CB}	60 V
P_{DISS}	60 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+125^\circ C$
θ_{JC}	1.9 $^\circ C/W$

PACKAGE STYLE .380" 4L STUD (MOD STUD)

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84
B	.980/24,89	
C	.370/9,40	.385/9,78
D	.004/0,10	.007/0,18
E	.320/8,13	.330/8,38
F	.100/2,54	.130/3,30
G	.450/11,43	.490/12,45
H	.090/2,29	.100/2,54
I	.155/3,94	.175/4,45
J		.750/19,05

1 = COLLECTOR 2 & 4 = EMITTER
3 = BASE

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CER}	$I_C = 50$ mA	$R_{BE} = 10 \Omega$		60			V
BV_{CBO}	$I_C = 50$ mA			60			V
BV_{CEO}	$I_C = 50$ mA			30			V
BV_{EBO}	$I_E = 10$ mA			4.0			V
h_{FE}	$V_{CE} = 25$ V	$I_C = 2.0$ A		20	45		---
C_{ob}	$V_{CB} = 30$ V	f = 1.0 MHz			90	120	pF
C_{re}	$V_{CE} = 30$ V	$I_C = 200$ mA	f = 1.0 MHz		55		pF
f_T	$V_{CE} = 25$ V	$I_C = 6.0$ A	f = 100 MHz		800		MHz